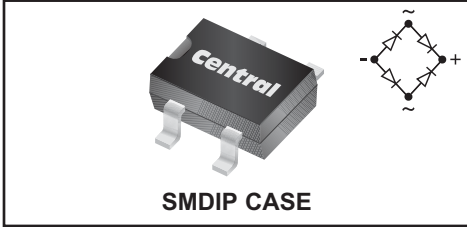


PRELIMINARY

CBRSDSH1-40L
SURFACE MOUNT
HIGH DENSITY
1 AMP LOW V_F SILICON
SCHOTTKY BRIDGE RECTIFIER



www.centrasemi.com



DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRSDSH1-40L is a full wave bridge rectifier mounted in a durable epoxy surface mount molded case, utilizing glass passivated chips.

MARKING: FULL PART NUMBER

FEATURES:

- Low Leakage Current (20 μ A TYP @ V_{RRM})
- Low V_F Schottky Diodes (440mV MAX @ $I_F=1.0A$)

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	40	V
DC Blocking Voltage	V_R	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Average Forward Current	I_O	1.2	A
Peak Repetitive Forward Current	I_{FRM}	1.7	A
Peak Forward Surge Current	I_{FSM}	20	A
Operating Junction Temperature	T_J	-50 to +125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-50 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

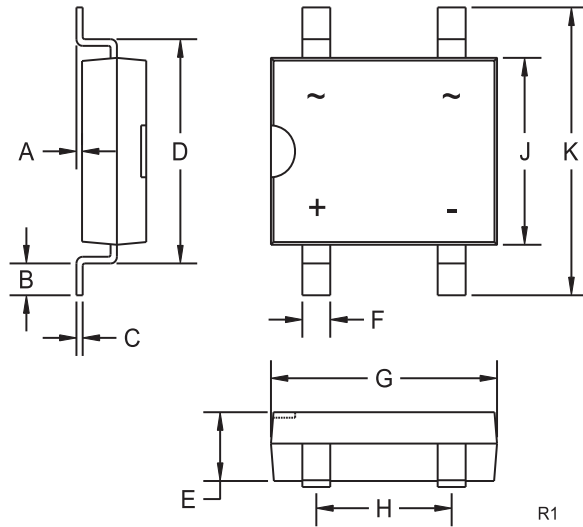
SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I_R	$V_R=40V$	20	50	μA
I_R	$V_R=40V, T_A=100^\circ\text{C}$	5.0	20	mA
V_F	$I_F=500\text{mA}$	360	380	mV
V_F	$I_F=1.0A$	390	440	mV
C_J	$V_R=4.0V, f=1.0\text{MHz}$	150		pF

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SMDIP CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

MARKING: FULL PART NUMBER

R1 (7-June 2010)